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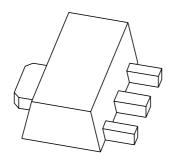
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BF621; BF623PNP high-voltage transistors

Product data sheet Supersedes data of 1999 Apr 21 2004 Dec 14



PNP high-voltage transistors

BF621; BF623

FEATURES

• Low current (max. 50 mA)

• High voltage (max. 300 V).

APPLICATIONS

Video output stages.

DESCRIPTION

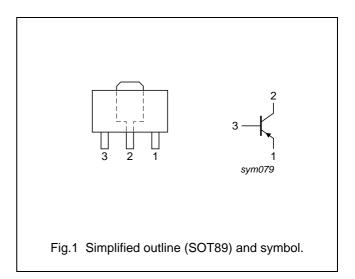
PNP high-voltage transistor in a SOT89 plastic package. NPN complements: BF620 and BF622.

MARKING

TYPE NUMBER	MARKING CODE
BF621	DF
BF623	DB

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NUMBER	NAME	DESCRIPTION	VERSION	
BF621	SC-62 plastic surface mounted package; collector pad for good h		SOT89	
BF623		transfer; 3 leads		

PNP high-voltage transistors

BF621; BF623

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

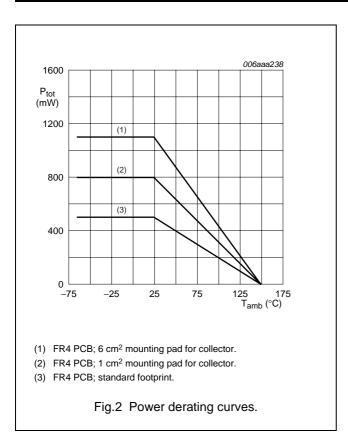
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BF621		_	-300	V
	BF623		_	-250	V
V_{CEO}	collector-emitter voltage	open base			
	BF621		_	-300	V
	BF623		_	-250	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-50	mA
I _{CM}	peak collector current		_	-100	mA
I _{BM}	peak base current		_	-50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
		note 1	_	0.5	W
		note 2	_	0.8	W
		note 3	_	1.1	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm².

PNP high-voltage transistors

BF621; BF623



PNP high-voltage transistors

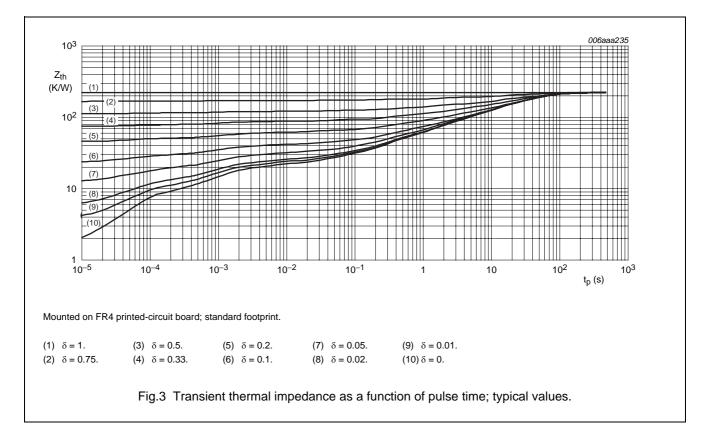
BF621; BF623

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to	in free air		
	ambient	note 1	250	K/W
		note 2	156	K/W
		note 3	113	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		30	K/W

Notes

- 1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
- 2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm².



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2004 Dec 14

PNP high-voltage transistors

BF621; BF623

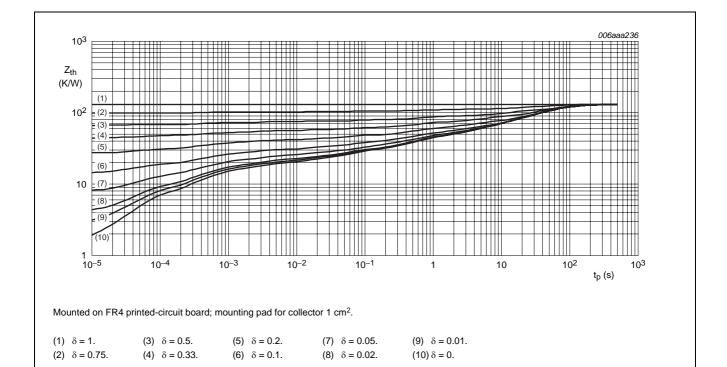
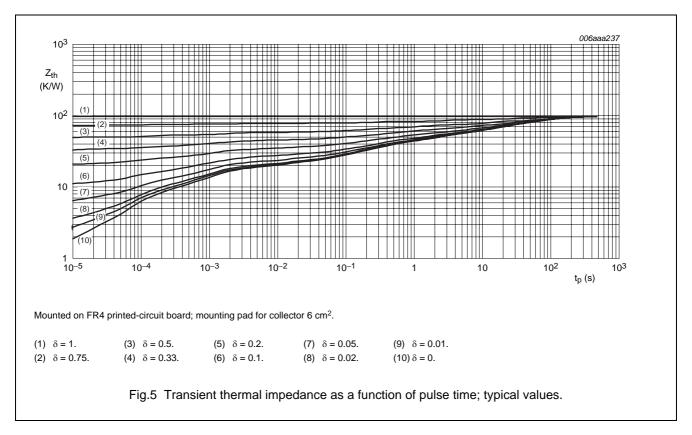


Fig.4 Transient thermal impedance as a function of pulse time; typical values.



PNP high-voltage transistors

BF621; BF623

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	I _E = 0 A; V _{CB} = -200 V	_	-10	nA
		$I_E = 0 \text{ A}; V_{CB} = -200 \text{ V}; T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I _{EBO}	emitter-base cut-off current	$I_C = 0 \text{ A}; V_{EB} = -5 \text{ V}$	_	-50	nA
h _{FE}	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}$	50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -30 \text{ mA}; I_B = -5 \text{ mA}$	_	-800	mV
C _{re}	feedback capacitance	$I_C = I_C = 0 \text{ A}; V_{CE} = -30 \text{ V}; f = 1 \text{ MHz}$	_	1.6	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; f = 100 \text{ MHz}$	60	_	MHz

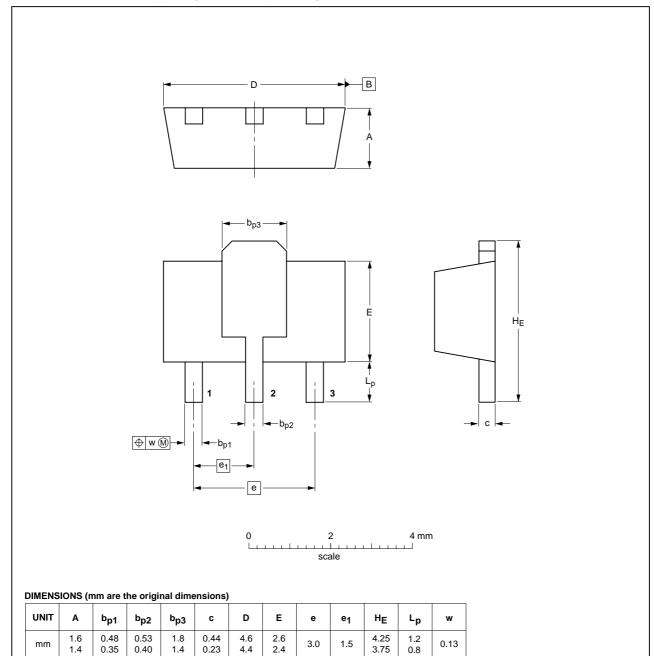
PNP high-voltage transistors

BF621; BF623

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DATE	
SOT89		TO-243	SC-62			-04-08-03 06-03-16

PNP high-voltage transistors

BF621; BF623

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: http://www.nxp.com
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